

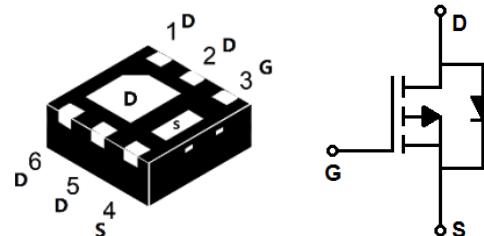
Features

- Low $R_{DS(on)}$ @ $V_{GS}=-4.5V$
- -2.5V Logic Level Control
- P Channel DFN2X2-6L Package
- Pb-Free, RoHS Compliant

$V_{(BR)DSS}$	$R_{DS(ON)}\text{ Typ}$	$I_D \text{ Max}$
-16V	18.2mΩ @ -4.5V	-10A
	25.2mΩ @ -2.5V	

Applications

- High-side Load Switch
- Switching Circuits
- High Speed line Driver


DFN2X2-6L
Order Information

Product	Package	Marking	Packing
DMP1005UFDF-7-CN	DNF2X2-6L	1216	4000PCS/Reel

Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

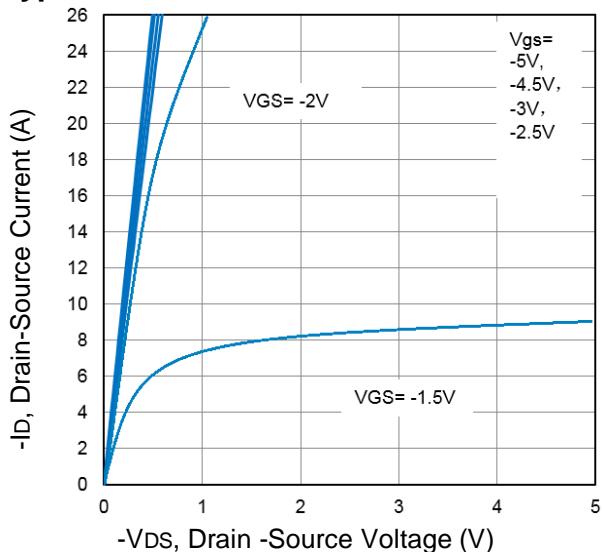
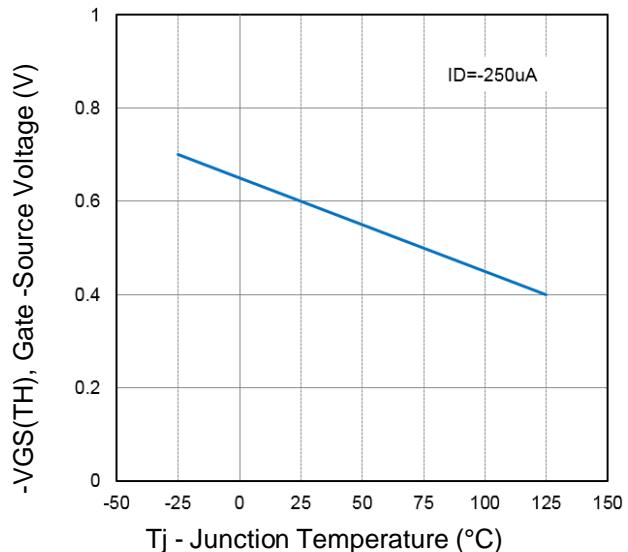
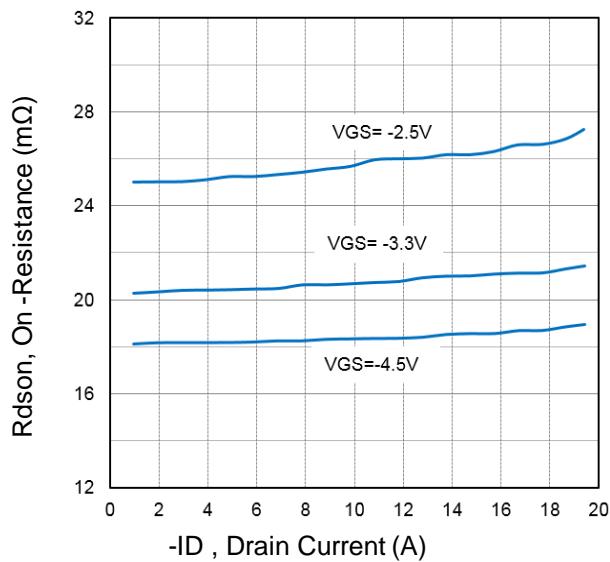
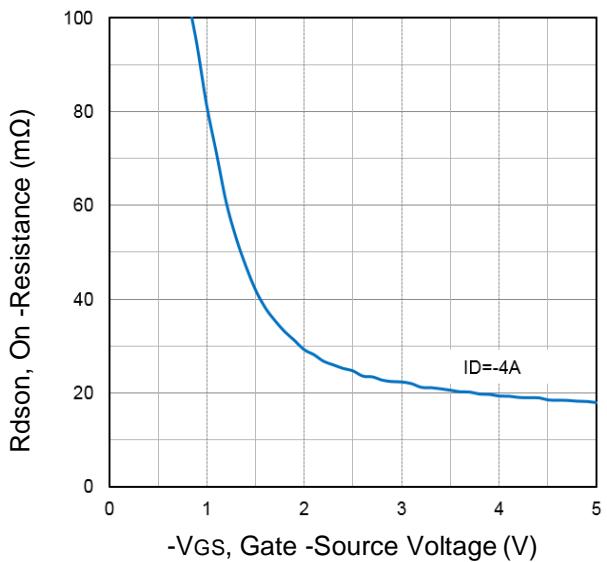
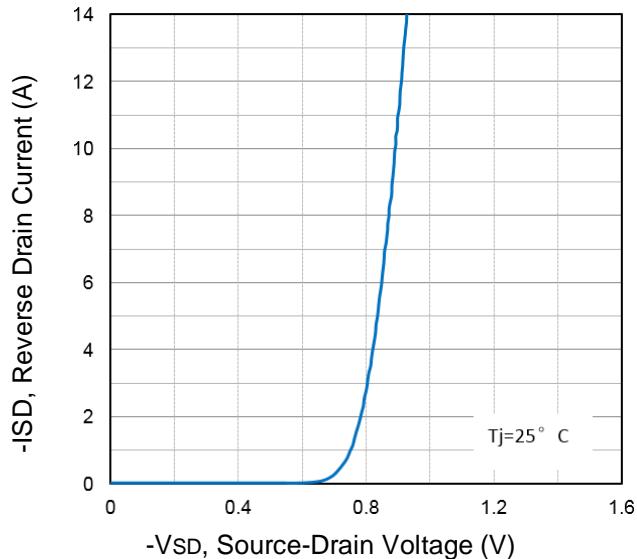
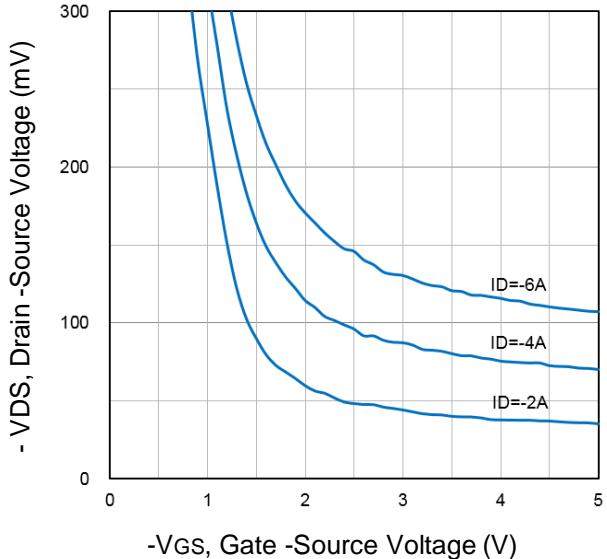
Symbol	Parameter	Rating	Unit
Common Ratings (TA=25°C Unless Otherwise Noted)			
V_{GS}	Gate-Source Voltage	±12	V
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	-16	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 150	°C
Mounted on Large Heat Sink			
I_{DM}	Pulse Drain Current Tested①	TA=25°C -32	A
I_D	Continuous Drain Current	TA=25°C -10	A
		TA=70°C -8	
P_D	Maximum Power Dissipation	TA=25°C 2.8	W
		TA=70°C 2.0	
R_{QA}	Thermal Resistance-Junction-Ambient	50	°C/W

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_D=-250\mu\text{A}$	-16	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current($T_A=25^\circ\text{C}$)	$V_{\text{DS}}=-16\text{V}, V_{\text{GS}}=0\text{V}$	--	--	-1	μA
	Zero Gate Voltage Drain Current($T_A=125^\circ\text{C}$)	$V_{\text{DS}}=-12\text{V}, V_{\text{GS}}=0\text{V}$	--	--	-100	μA
I_{GSS}	Gate-Body Leakage Current	$V_{\text{GS}}=\pm 12\text{V}, V_{\text{DS}}=0\text{V}$	--	--	± 100	nA
$V_{\text{GS}(\text{TH})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_D=-250\mu\text{A}$	-0.4	-0.6	-1.2	V
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance②	$V_{\text{GS}}=-4.5\text{V}, I_D=4\text{A}$	--	18.2	22	$\text{m}\Omega$
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance②	$V_{\text{GS}}=-3.3\text{V}, I_D=3\text{A}$	--	20.8	25	$\text{m}\Omega$
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance②	$V_{\text{GS}}=-2.5\text{V}, I_D=2\text{A}$	--	25.2	30	$\text{m}\Omega$
Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)						
C_{iss}	Input Capacitance	$V_{\text{DS}}=-10\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$	--	1443	--	pF
C_{oss}	Output Capacitance		--	235	--	pF
C_{rss}	Reverse Transfer Capacitance		--	211	--	pF
Q_g	Total Gate Charge	$V_{\text{DS}}=-10\text{V}, I_D=-4\text{A}, V_{\text{GS}}=-5\text{V}$	--	15.4	--	nC
Q_{gs}	Gate Source Charge		--	2.0	--	nC
Q_{gd}	Gate Drain Charge		--	3.6	--	nC
Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)						
$t_{\text{d}(\text{on})}$	Turn on Delay Time	$V_{\text{DD}}=-10\text{V}, I_D=-1\text{A}, R_G=3.3\Omega, V_{\text{GS}}=-4.5\text{V}$	--	8	--	ns
t_r	Turn on Rise Time		--	15.5	--	ns
$t_{\text{d}(\text{off})}$	Turn Off Delay Time		--	42	--	ns
t_f	Turn Off Fall Time		--	10.5	--	ns
Source Drain Diode Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)						
I_{SD}	Source drain current(Body Diode)	$T_A=25^\circ\text{C}$	--	--	-10	A
V_{SD}	Forward on voltage②	$T_j=25^\circ\text{C}, I_{\text{SD}}=-2\text{A}, V_{\text{GS}}=0\text{V}$	--	--	-1.2	V

Notes:

① Pulse width limited by maximum allowable junction temperature

②Pulse test ; Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

Typical Characteristics

Fig1. Typical Output Characteristics

Fig2. Normalized Threshold Voltage Vs. Temperature

Fig3. On-Resistance vs. Drain Current and Gate

Fig4. On-Resistance vs. Gate Source Voltage

Fig5. Typical Source-Drain Diode Forward Voltage

Fig6. Drain-Source Voltage vs Gate-Source Voltage

Typical Characteristics

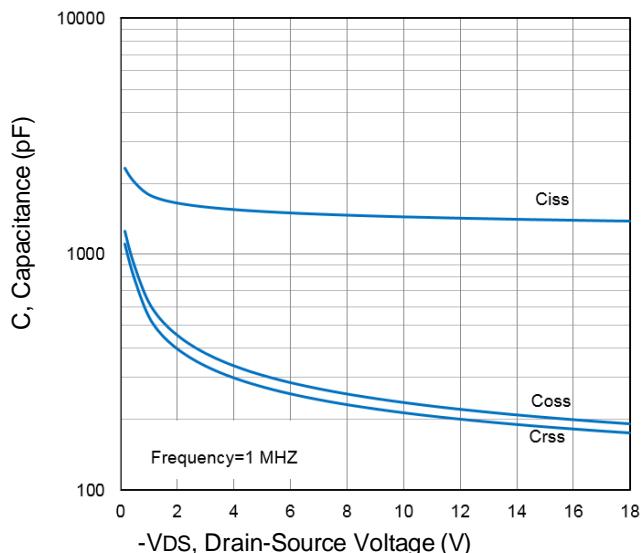


Fig7. Typical Capacitance Vs. Drain-Source Voltage

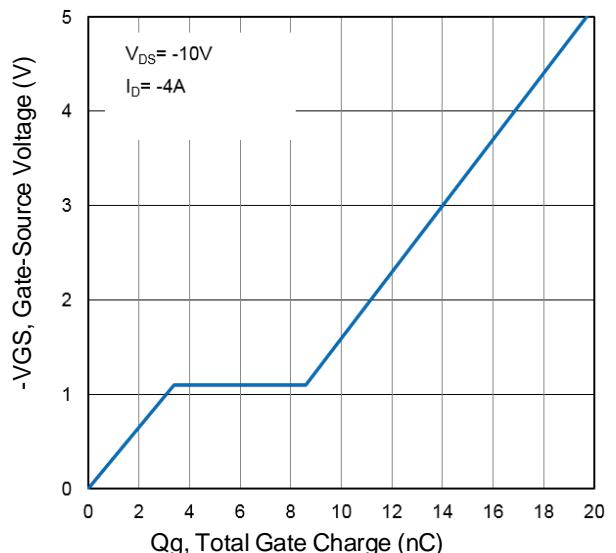


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

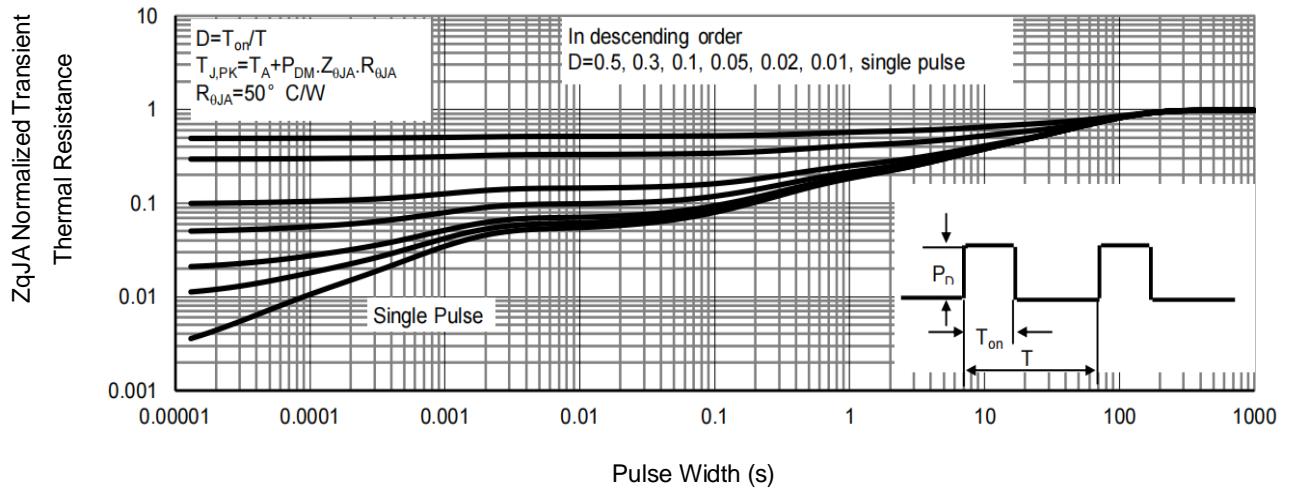


Fig9. Normalized Maximum Transient Thermal Impedance

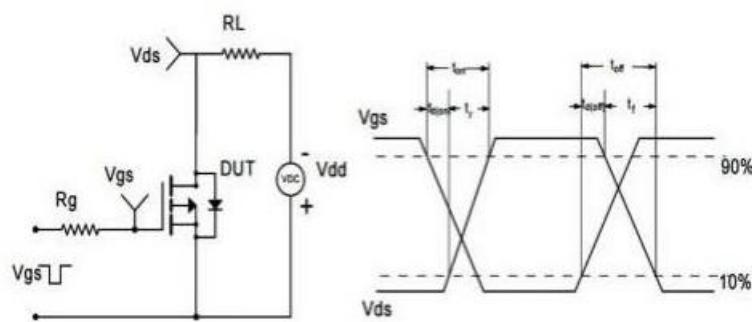
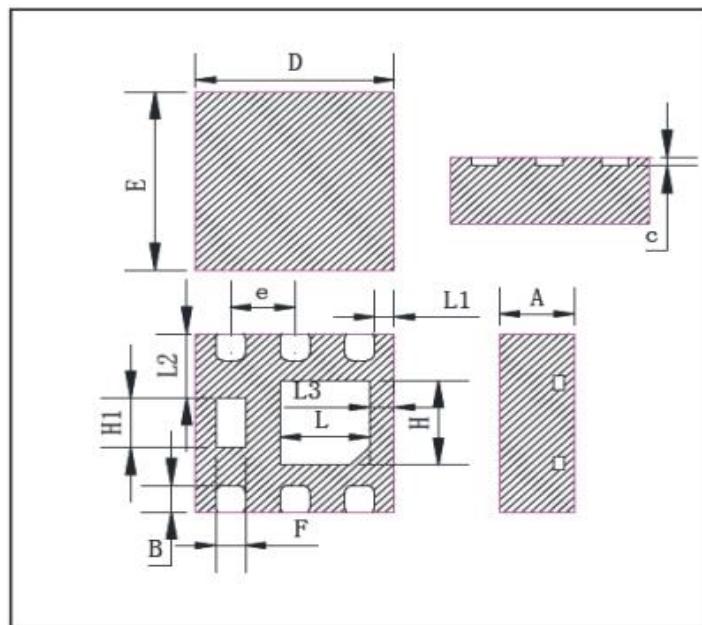


Fig10. Switching Time Test Circuit and waveforms

DFN2X2-6L Mechanical Data


Symbol	Min	Typ	Max
A	0.70	0.75	0.80
B	0.25	0.30	0.35
C	0.153	0.203	0.253
D	1.90	2.00	2.10
E	1.90	2.00	2.10
e	0.60	0.65	0.70
F	0.25	0.30	0.35
H	0.85	0.95	1.05
H1	0.51	0.56	0.61
L	0.80	0.90	1.00
L1	0.15	0.20	0.25
L2	0.62	0.72	0.82
L3	0.25	0.30	0.35

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